



LED940D-05

- Infrared Light Emitting Diode
- 940 nm, 25 mW
- InGaAs structure
- 5mm clear epoxy resin



Description

LED940D-05 is an **AlGaAs** based infrared LED, typically emitting at 940 nm with a typical output power of 25 mW. **LED940D-05** features a 350x350µm chip die in a hermetically sealed 5 mm clear epoxy resin.

Maximum Rating (T_{CASE} = 25°C)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	P _D		170	mW
Forward Current	I _F		100	mA
Pulse Forward Current*	I _{FP}		1000	mA
Reverse Voltage	V _R		5	V
Thermal Resistance	R _{thja}		170	K/W
Junction Temperature	T _J		120	°C
Operating Temperature	T _{OPR}	- 40	+ 100	°C
Storage Temperature	T _{STG}	- 40	+ 100	°C
Soldering Temperature (max 3s)	T _{SOL}		+ 265	°C

* **Duty cycle = 1%, pulse width = 10 µs**



Electro-Optical Characteristics (T_{CASE} = 25°C, I_F = 50 mA)

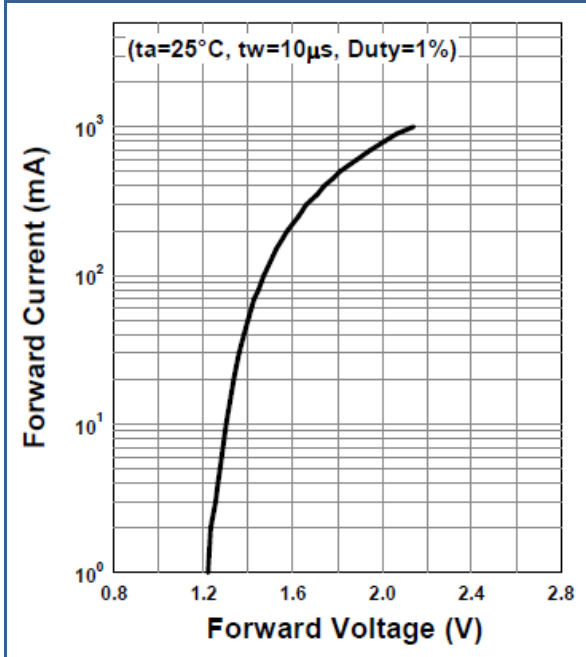
Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	λ _P	930	940	955	nm
Spectral Width (FWHM)	Δλ		40		nm
Forward Voltage	V _F		1.4	1.7	V
	V _{F PULSE}		2.1*		V
Radiated Power	P _O		25		mW
	P _{O PULSE}		400		mW
Radiant Intensity	I _E		9.3		mW/sr
	I _{E PULSE}		150		mW/sr
Viewing Half Angle	Θ _{1/2}		± 45		deg.
Rise/Fall Time	t _r		10/15		ns

***Pulse Condition: Duty cycle = 1%, pulse width = 10 µs, pulse current = 1A**

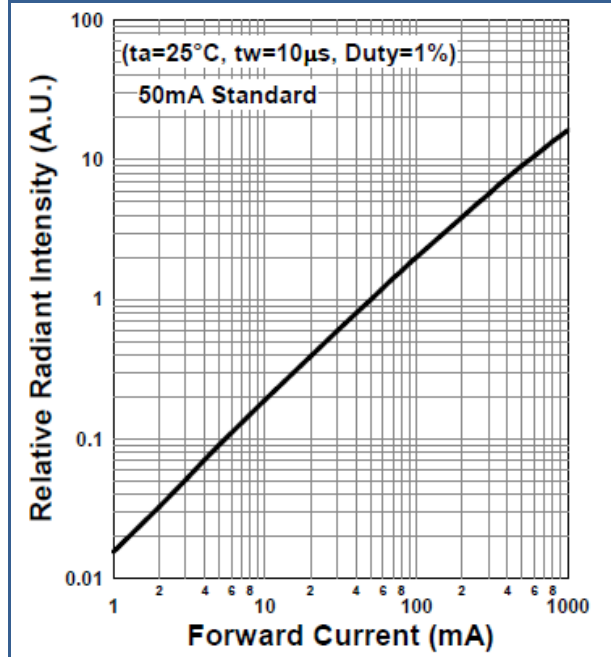


Performance Characteristics

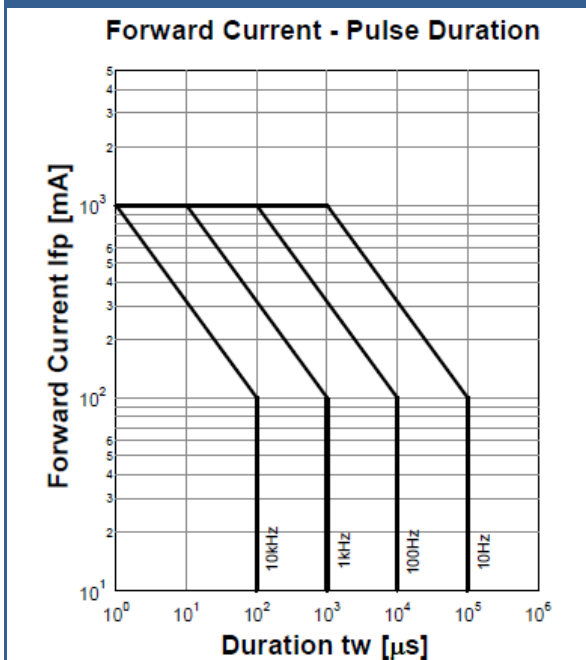
Forward Current vs. Forward Voltage



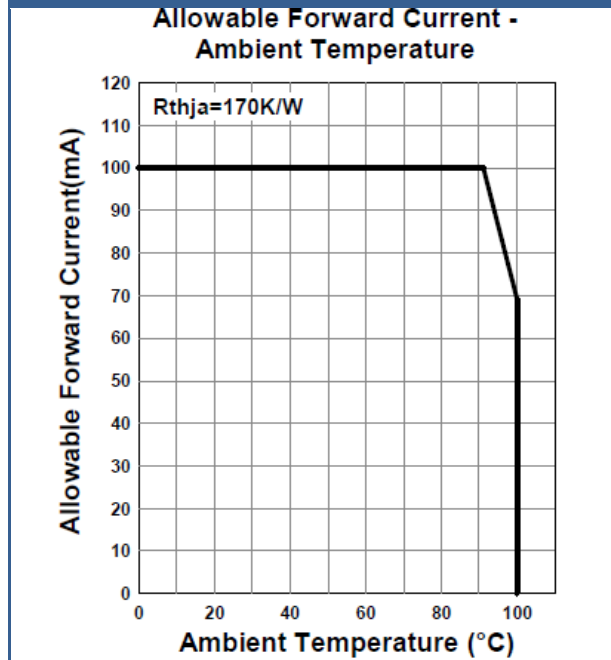
Relative Radiant Intensity vs. Forward Current



Forward Current vs. Pulse Duration



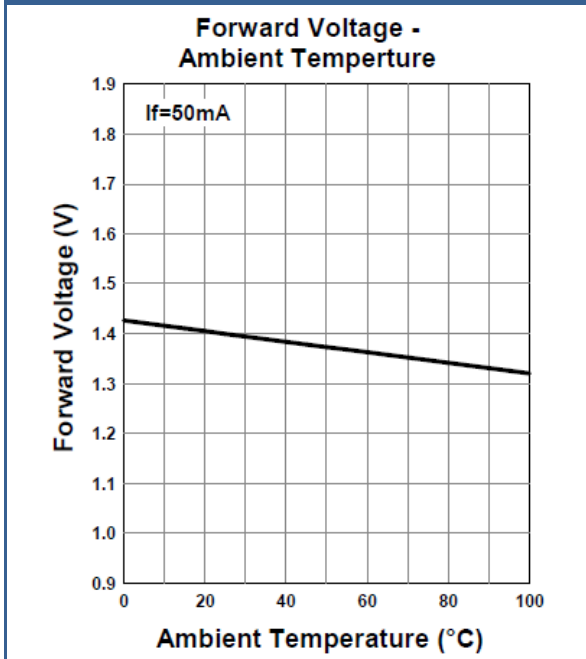
Allowable Forward Current vs. Ambient Temp.



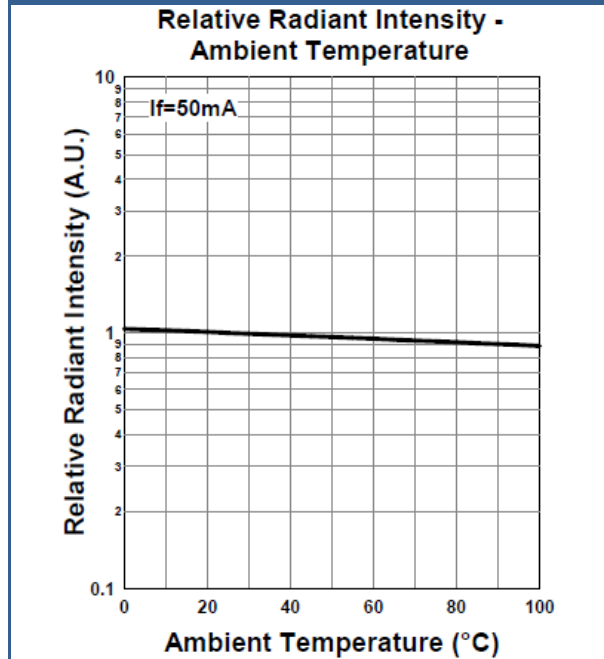


Performance Characteristics

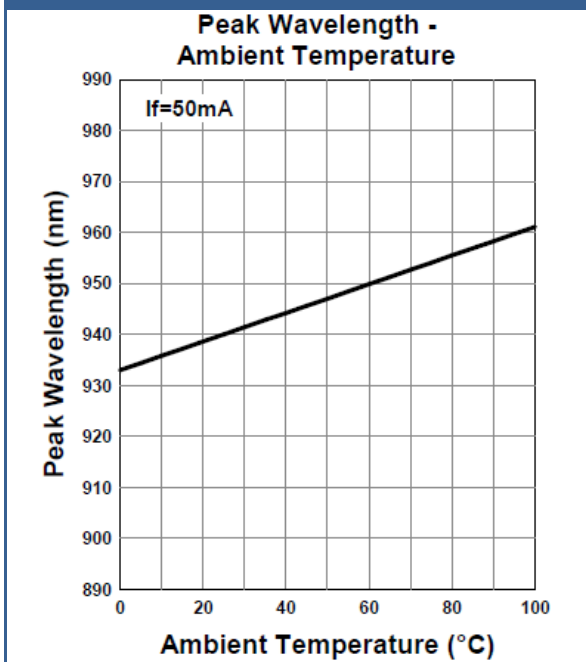
Forward Voltage vs. Ambient Temperature



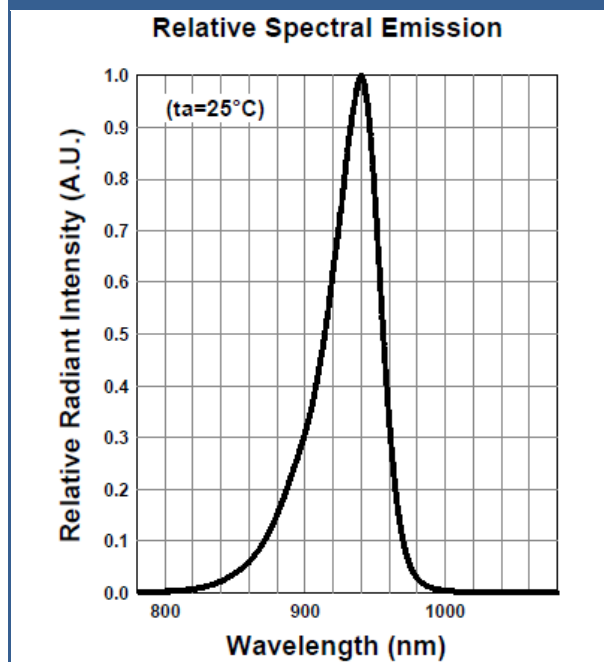
Relative Radiant Intensity vs. Ambient Temp.



Peak Wavelength vs. Ambient Temperature

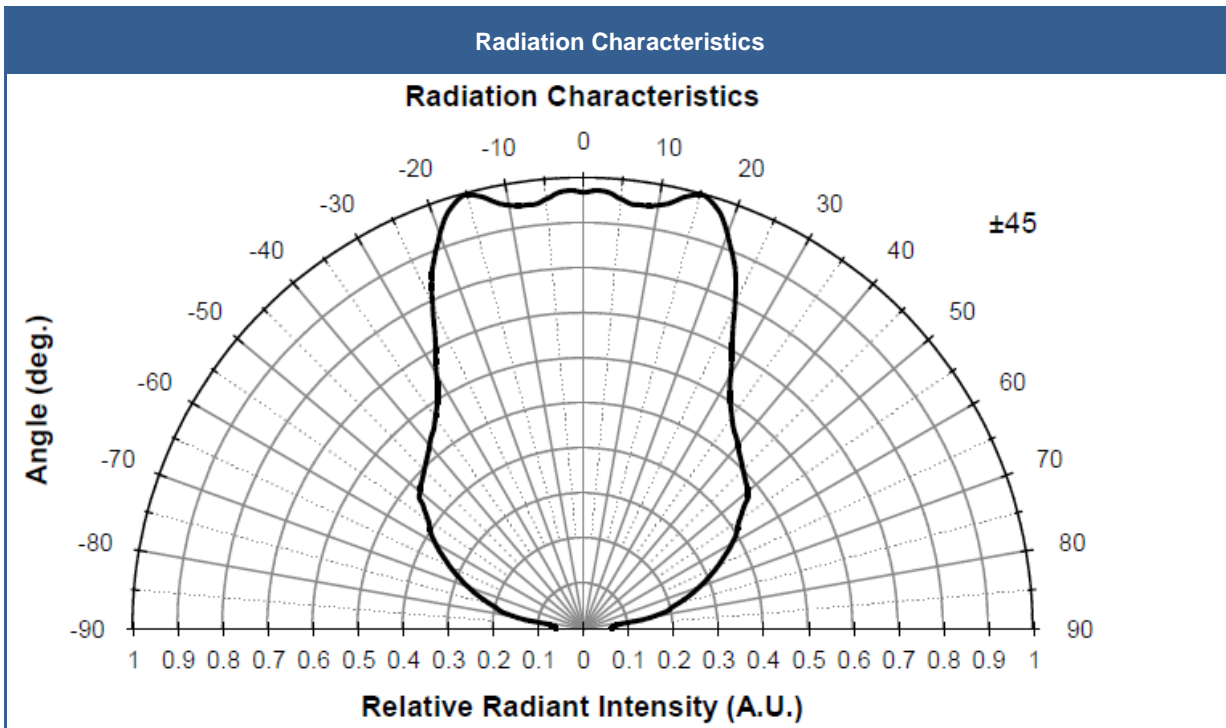


Relative Spectral Emission

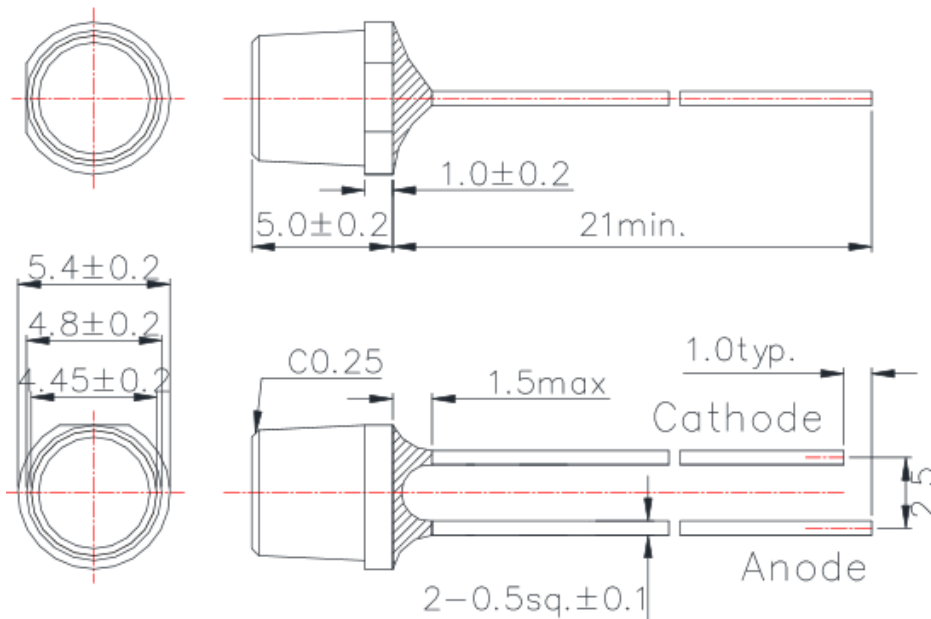




Performance Characteristics



Outline Dimensions



All dimensions in mm